ABSTRACT OF THE DISCLOSURE

A method ~~of preparing in~~ is provided for preparing, with high reproducibility, a carbon-doped group III-V compound semiconductor crystal having favorable electrical characteristics and having impurities removed therefrom, and in which the amount of doped carbon can be adjusted easily during crystal growth ~~is provided~~. This method ~~of preparing a carbon-doped group III-V compound semiconductor crystal~~ includes the steps of: filling a crucible with compound raw material, solid carbon, and boron oxide; sealing the crucible filled ~~with compound material, solid carbon, and boron oxide~~ within an airtight vessel formed of a gas impermeable material; heating and melting the compound raw material under the sealed state in the airtight vessel; and solidifying the melted compound raw material to grow a carbon-doped compound semiconductor crystal.